

## 1. General description

Planar passivated high commutation three quadrant triac in a SOT54 (TO-92) plastic package. This "series D" triac balances the requirements of commutation performance and gate sensitivity and is intended for interfacing with low power drivers and logic ICs including microcontrollers.

## 2. Features and benefits

- · 3Q technology for improved noise immunity
- Direct gate triggering from low power drivers and logic ICs
- · High commutation capability with very sensitive gate
- High voltage capability
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only
- Very sensitive gate for easy logic level triggering

### 3. Applications

- Low power motor controls
- Small inductive loads e.g. solenoids, door locks, water valves
- Small loads in large white goods

### 4. Quick reference data

#### Table 1. Quick reference data

		12	 			
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DRM</sub>	repetitive peak off- state voltage		-	-	800	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_{lead} \le 70 \text{ °C}$ ; <u>Fig. 1</u> ; Fig. 2; Fig. 3	-	-	0.8	A
	non-repetitive peak on- state current	full sine wave; T <sub>j(init)</sub> = 25 °C; t <sub>p</sub> = 20 ms; <u>Fig. 4</u> ; <u>Fig. 5</u>	-	-	9	A
		full sine wave; T <sub>j(init)</sub> = 25 °C; t <sub>p</sub> = 16.7 ms	-	-	9.9	A
Tj	junction temperature		-	-	125	°C
Static charact	eristics					
I <sub>GT</sub>	gate trigger current	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	0.25	-	5	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G-; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	0.25	-	5	mA

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G-; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	0.25	-	5	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	-	10	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 0.85 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.35	1.6	V
Dynamic chai	acteristics					
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 536 V; T <sub>j</sub> = 125 °C; (V <sub>DM</sub> = 67% of V <sub>DRM</sub> ); exponential waveform; gate open circuit	200	-	-	V/µs
dl <sub>com</sub> /dt	rate of change of commutating current	$\label{eq:VD} \begin{array}{l} V_D = 400 \text{ V};  T_j = 125 \ ^\circ\text{C}; \\ I_{T(\text{RMS})} = 0.8  \text{A};  \text{dV}_{\text{com}}/\text{dt} = 10  \text{V}/\mu\text{s}; \\ \text{gate open circuit} \end{array}$	0.5	-	-	A/ms

# 5. Pinning information

Table 2. F	Pinning inf	ormation		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T2	main terminal 2		T2-71
2	G	gate		sym051
3	Τ1	main terminal 1	TO-92 (SOT54)	Symoor

# 6. Ordering information

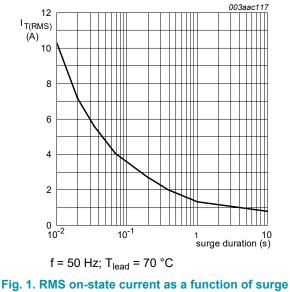
Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
BTA2008-800D	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54			

### 7. Limiting values

### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DRM</sub>	repetitive peak off-state voltage		-	800	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_{lead} \le 70 \text{ °C}$ ; <u>Fig. 1</u> ; <u>Fig. 2</u> ; Fig. 3	-	0.8	A
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 20 ms; Fig. 4; Fig. 5	-	9	A
		full sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 16.7 ms	-	9.9	А
l <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; SIN	-	0.41	A²s
dl <sub>T</sub> /dt	rate of rise of on-state current	I <sub>G</sub> = 20 mA	-	100	A/µs
I <sub>GM</sub>	peak gate current		-	1	А
P <sub>GM</sub>	peak gate power		-	2	W
P <sub>G(AV)</sub>	average gate power	over any 20 ms period	-	0.1	W
T <sub>stg</sub>	storage temperature		-40	150	°C
T <sub>i</sub>	junction temperature		-	125	°C



duration; maximum values

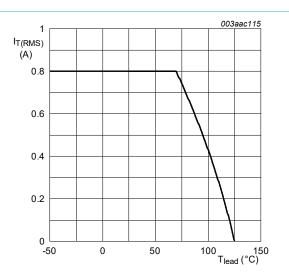
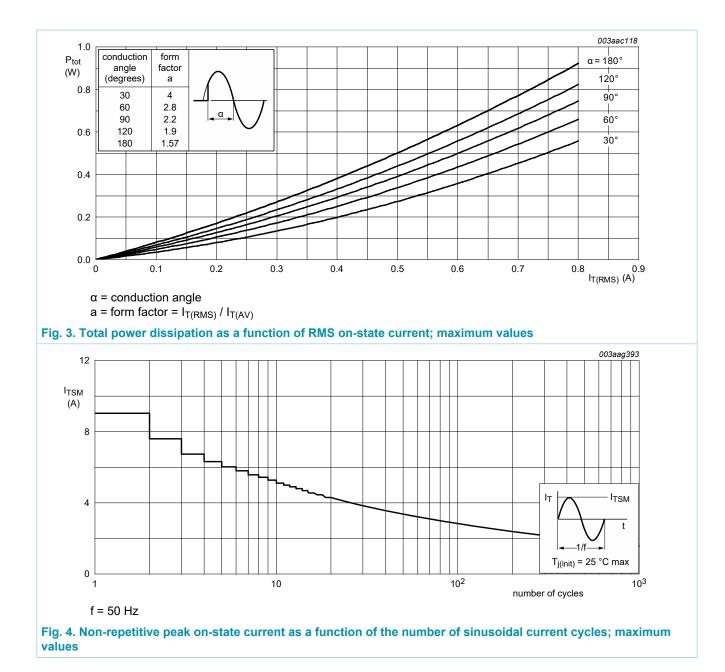


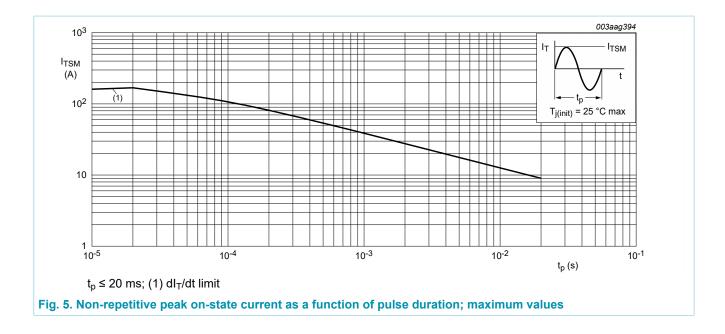
Fig. 2. RMS on-state current as a function of lead temperature; maximum values

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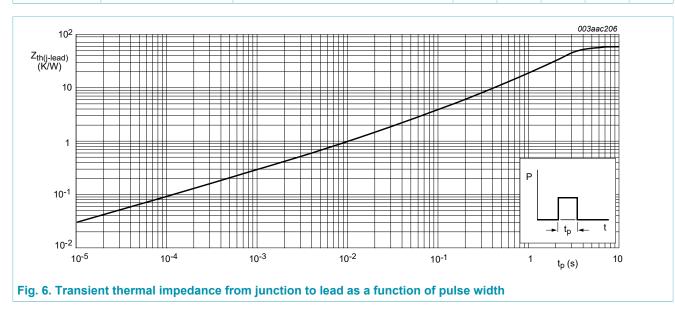
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## 8. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-lead)}$	thermal resistance from junction to lead	full cycle; <u>Fig. 6</u>	-	-	60	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air	printed circuit board mounted: lead length = 4 mm	-	150	-	K/W



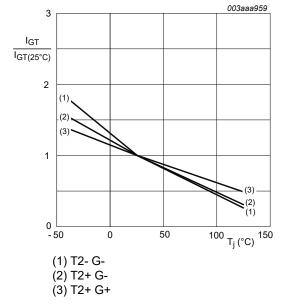
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## 9. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
I <sub>GT</sub>	gate trigger current	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	0.25	-	5	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2+ G-};$ T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	0.25	-	5	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G-; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	0.25	-	5	mA
ΙL	latching current	$V_D$ = 12 V; I <sub>G</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; <u>Fig. 8</u>	-	-	10	mA
		V <sub>D</sub> = 12 V; I <sub>G</sub> = 0.1 A; T2+ G-; T <sub>j</sub> = 25 °C; <u>Fig. 8</u>	-	-	20	mA
		V <sub>D</sub> = 12 V; I <sub>G</sub> = 0.1 A; T2- G-; T <sub>j</sub> = 25 °C; <u>Fig. 8</u>	-	-	10	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	-	10	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 0.85 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.35	1.6	V
V <sub>GT</sub>	gate trigger voltage	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>	-	0.9	1.5	V
		V <sub>D</sub> = 400 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 125 °C; <u>Fig. 11</u>	0.2	0.3	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 800 V; T <sub>j</sub> = 125 °C	-	0.1	0.5	mA
Dynamic ch	naracteristics		·			
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 536 V; T <sub>j</sub> = 125 °C; (V <sub>DM</sub> = 67% of V <sub>DRM</sub> ); exponential waveform; gate open circuit	200	-	-	V/µs
dl <sub>com</sub> /dt	rate of change of commutating current	$V_D$ = 400 V; T <sub>j</sub> = 125 °C; I <sub>T(RMS)</sub> = 0.8 A; dV <sub>com</sub> /dt = 10 V/µs; gate open circuit	0.5	-	-	A/ms

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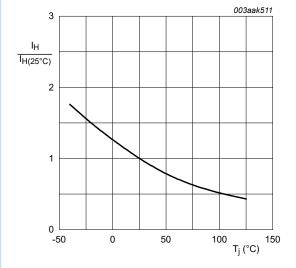
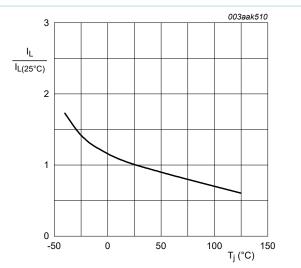
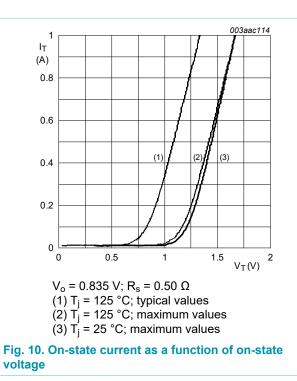


Fig. 9. Normalized holding current as a function of junction temperature

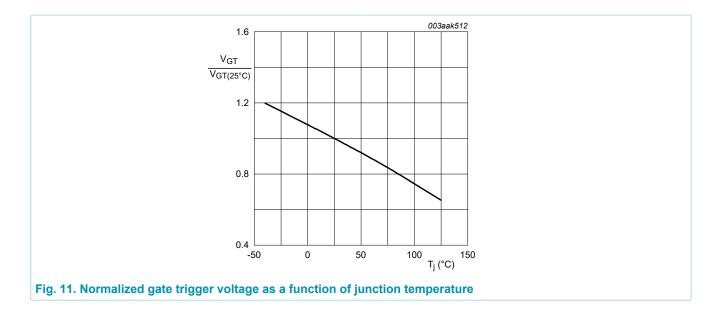






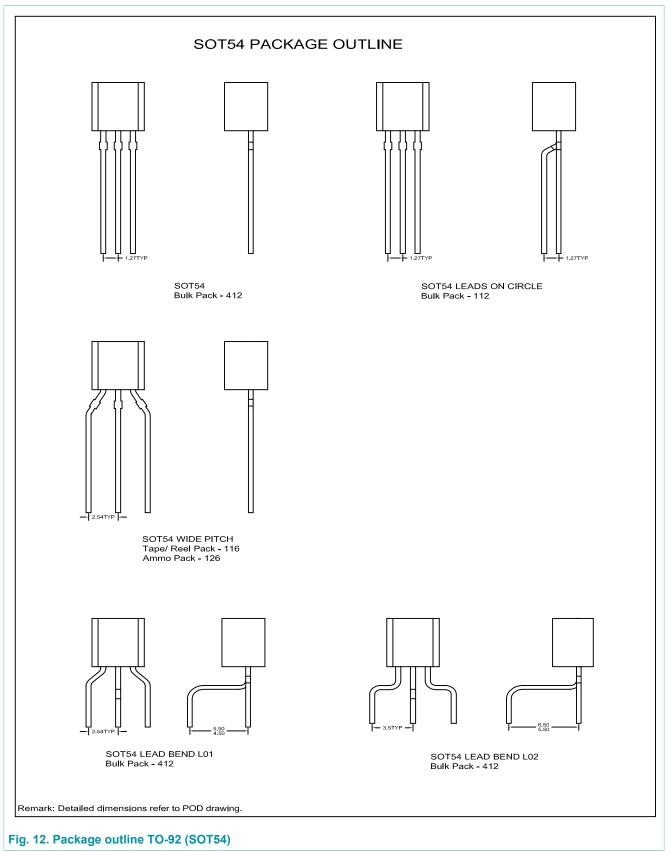
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# **10. Package outline**



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#### **3Q Hi-Com Triac**

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Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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